

RoHS

COMPLIANT HALOGEN

FREE Available

AUIRF7304QTRPBF-VB Datasheet Dual P-Channel 20V (D-S) MOSFET

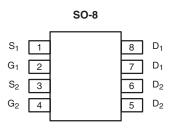
PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)			
	0.018 at V _{GS} = - 4.5 V	- 8.9			
- 20	0.022 at V _{GS} = - 2.5 V	- 8.1			
	0.030 at V _{GS} = - 1.8 V	- 3.6			

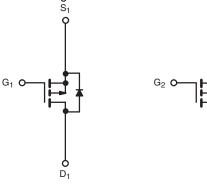
FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- Advanced High Cell Density Process
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

Load Switching





P-Channel MOSFET

D₂ P-Channel MOSFET

S₂

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 20		v
Gate-Source Voltage		V _{GS}	± 12		v
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	– I _D	- 8.9	- 6.7	
	T _A = 70 °C		- 7.1	- 5.4	
Pulsed Drain Current		I _{DM}	- 30		A
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.7	- 0.9	
	T _A = 25 °C	- P _D	2.0	1.1	w
Maximum Power Dissipation ^a	T _A = 70 °C		1.3	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 t	o 150	°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 10 s	R _{thJA}	46	62.5		
Maximum Junction-to-Ambient ^a	Steady State		80	110	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	24	32		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions M		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -350 \ \mu A$	- 0.4		- 1.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA	
Zara Cata Valtaga Drain Current	1	$V_{DS} = -20 V, V_{GS} = 0 V$	- 1 - 5		- 1		
Zero Gate Voltage Drain Current	IDSS	V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 55 °C			μΑ		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -4.5 V$	- 30			А	
		V _{GS} = - 4.5 V, I _D = - 8.9 A		0.018		Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 8.1 A		0.022			
		V _{GS} = - 1.8 V, I _D = - 3.6 A		0.030			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 8.9 A		26		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 1.7 A, V _{GS} = 0 V		- 0.7	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg			34.5	52		
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 8.9 A		5.1		nC	
Gate-Drain Charge	Q _{gd}			9.6			
Gate Resistance	Rg			9		Ω	
Turn-On Delay Time	t _{d(on)}			25	40		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 6 Ω		46	70		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_g = 6 Ω		230	345	ns	
Fall Time	t _f			155	235		
Source-Drain Reverse Recovery Time	ery Time t _{rr} I _F = - 1.7 A, dl/dt = 100 A/µs			128	200		

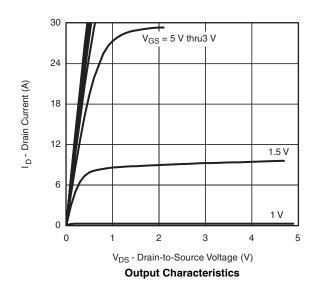
Notes:

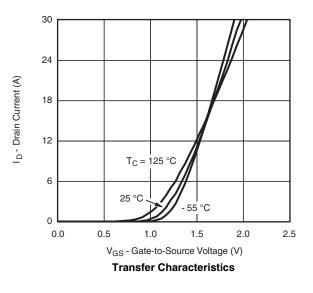
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C unless otherwise noted

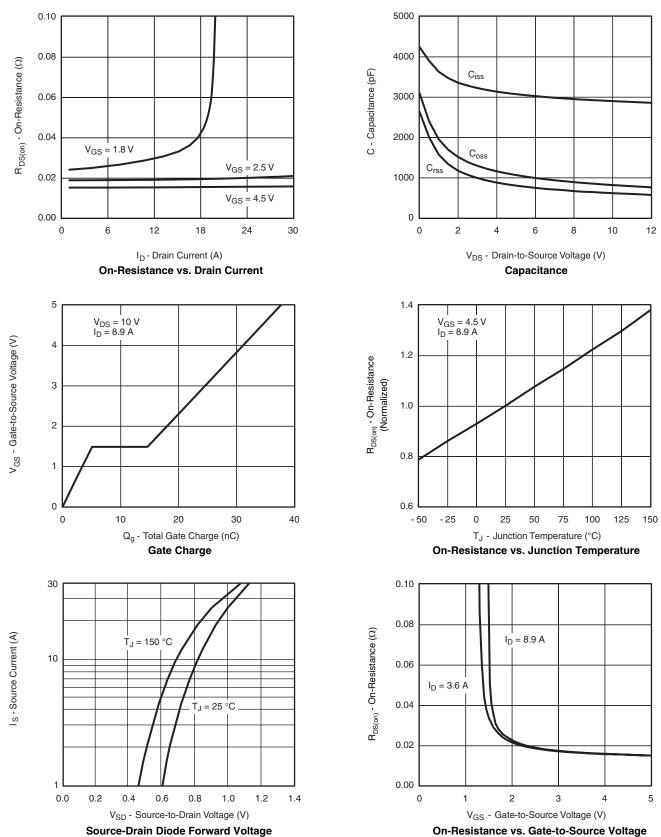




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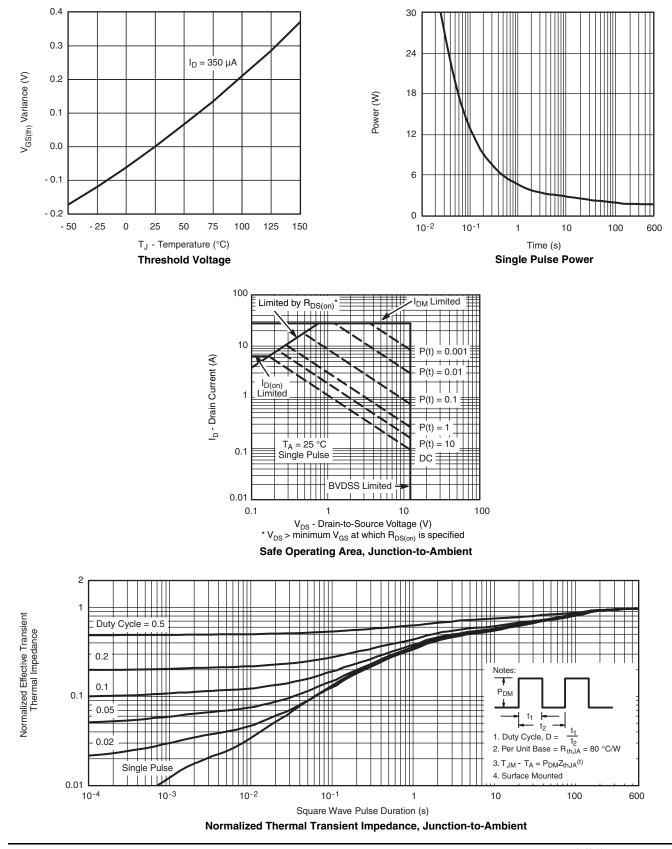
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服务热线:400-655-8788

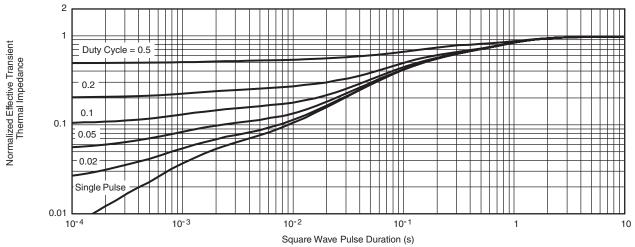


TYPICAL CHARACTERISTICS 25 °C unless otherwise noted





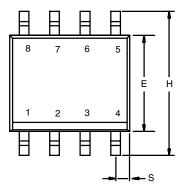
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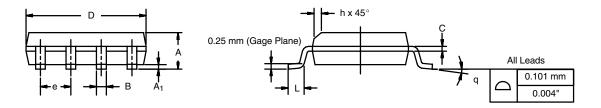


Normalized Thermal Transient Impedance, Junction-to-Foot



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012



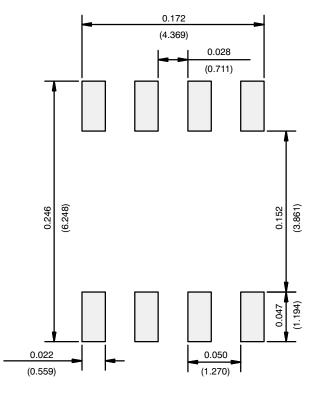


	MILLIM	IETERS	INC	HES		
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

AUIRF7304QTRPBF-VB



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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